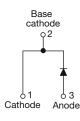
VS-HFA08TB120-M3

Vishay Semiconductors

HEXFRED[®] Ultrafast Soft Recovery Diode, 8 A



www.vishay.com



PRIMARY CHARACTERISTICS					
I _{F(AV)}	8 A				
V _R	1200 V				
V _F at I _F	2.4 V				
t _{rr} typ.	28 ns				
T _J max.	150 °C				
Package	TO-220AC 2L				
Circuit configuration	Single				

FEATURES

- Ultrafast and ultrasoft recovery
- Very low I_{RRM} and Q_{rr}
- \bullet Designed and qualified according to JEDEC $^{\circledast}\text{-}\text{JESD}$ 47
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

BENEFITS

- Reduced RFI and EMI
- · Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- Reduced parts count

DESCRIPTION

VS-HFA08TB120 is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 1200 V and 8 A continuous current, the VS-HFA08TB120 is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I_{BBM}) and does not exhibit any tendency to "snap-off" during the t_b portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA08TB120 is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Cathode to anode voltage	V _R		1200	V		
Maximum continuous forward current	I _F	T _C = 100 °C	8			
Single pulse forward current	I _{FSM}		130	А		
Maximum repetitive forward current	I _{FRM}		32			
Maximum neuror dissinction	P _D	T _C = 25 °C	73.5	W		
Maximum power dissipation		T _C = 100 °C	29	vv		
Operating junction and storage temperature range	T _J , T _{Stg}		-55 to +150	°C		

Revision: 16-Dec-2021



For technical questions within your region: <u>DiodesAmericas@vishay.com</u>, <u>DiodesAsia@vishay.com</u>, <u>DiodesEurope@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u>





www.vishay.com

Vishay Semiconductors

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS		
Cathode to anode breakdown voltage	V _{BR}	I _R = 100 μA	1200	-	-			
	V _{FM}	I _F = 8.0 A	-	2.6	3.3	V		
Maximum forward voltage		I _F = 16 A	-	3.4	4.3			
		I _F = 8.0 A, T _J = 125 °C	-	2.4	3.1			
Maximum reverse		$V_{R} = V_{R}$ rated	-	0.31	10			
leakage current	IRM	$T_J = 125 \text{ °C}, V_R = 0.8 \text{ x } V_R \text{ rated}$	-	135	1000	μA		
Junction capacitance	CT	V _R = 200 V	-	11	20	pF		
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8.0	-	nH		

DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25 \degree C$ unless otherwise specified)								
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS	
	t _{rr}	$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t = 200$	A/μs, V _R = 30 V	-	28	-		
Reverse recovery time	t _{rr1}	T _J = 25 °C		-	63	95	ns	
	t _{rr2}	T _J = 125 °C	I _F = 8.0 A dI _F /dt = 200 A/μs V _R = 200 V	-	106	160		
Deal and a second	I _{RRM1}	T _J = 25 °C		-	4.5	8.0		
Peak recovery current	I _{RRM2}	T _J = 125 °C		-	6.2	11	A	
Poweree recevery charge	Q _{rr1}	T _J = 25 °C		-	140	380	nC	
Reverse recovery charge	Q _{rr2}	T _J = 125 °C		-	335	880	nc	
Peak rate of recovery current	dl _{(rec)M} /dt1	T _J = 25 °C		-	133	-	A/µs	
during t _b	dl _{(rec)M} /dt2	T _J = 125 °C		-	85	-	γγµs	

THERMAL - MECHANICAL SPECIFICATIONS								
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS		
Lead temperature	T _{lead}	0.063" from case (1.6 mm) for 10 s	-	-	300	°C		
Thermal resistance, junction to case	R _{thJC}		-	-	1.7			
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount	-	-	40	K/W		
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth, and greased	-	0.25	-			
Weight			-	6.0	-	g		
weight			-	0.21	-	oz.		
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)		
Marking device		Case style 2L TO-220AC		HFA08	3TB120			

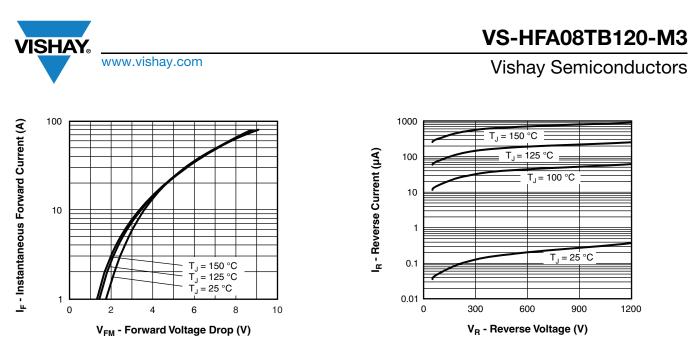


Fig. 1 - Maximum Forward Voltage Drop Characteristics



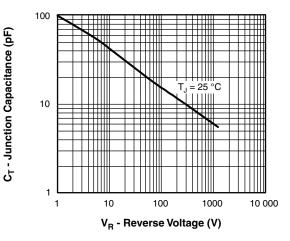


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

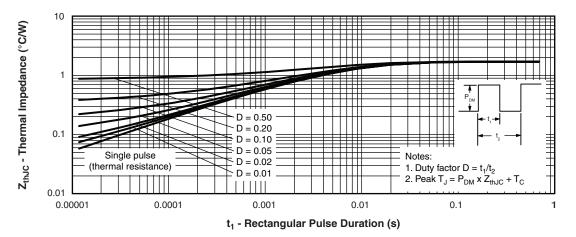
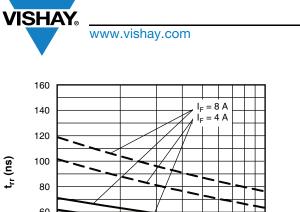


Fig. 4 - Maximum Thermal Impedance ZthJC Characteristics



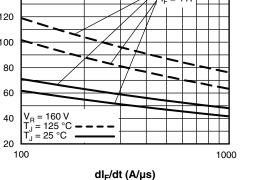


Fig. 5 - Typical Reverse Recovery Time vs. dl_F/dt

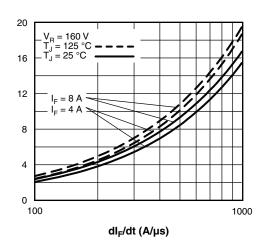
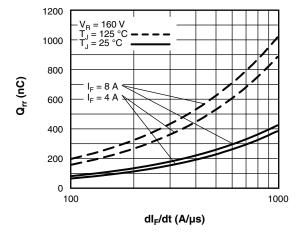


Fig. 6 - Typical Recovery Current vs. dl_F/dt





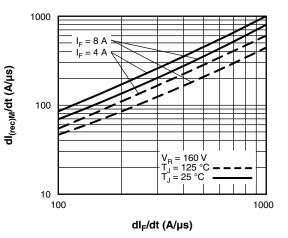


Fig. 8 - Typical $dI_{(rec)M}/dt$ vs. dI_F/dt

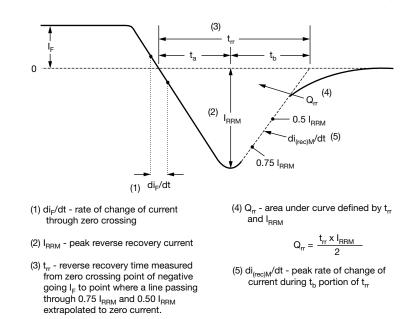


Fig. 9 - Reverse Recovery Waveform and Definitions

Revision: 16-Dec-2021	4	Document Number: 96189
For technical questions within your region	n: <u>DiodesAmericas@vishay.com</u> , <u>DiodesAsia@vishay.cc</u>	om, <u>DiodesEurope@vishay.com</u>
	GE WITHOUT NOTICE. THE PRODUCTS DESCRIBED	
ARE SUBJECT TO SPE	CIFIC DISCLAIMERS, SET FORTH AT www.vishay.com	<u>n/doc?91000</u>

I_{rr} (A)

VS-HFA08TB120-M3

Vishay Semiconductors

VS-HFA08TB120-M3



ORDERING INFORMATION TABLE

www.vishay.com

SHAY

Device code	VS-	HF	Α	08	тв	120	-МЗ
		2	3	4	5	6	7
	1 · 2 ·		nay Sem KFRED [®]	niconduo family	ctors pr	oduct	
	3 -	Elec	ctron irra	,	9 (1)		
	5	- Pac	kage:		,		
	6	. –		-220AC ng (120		V)	
	7 -			ntal digit gen-free		compli	ant and

ORDERING INFORMATION (Example)					
PREFERRED P/N	BASE QUANTITY	PACKAGING DESCRIPTION			
VS-HFA08TB120-M3	50	Antistatic plastic tube			

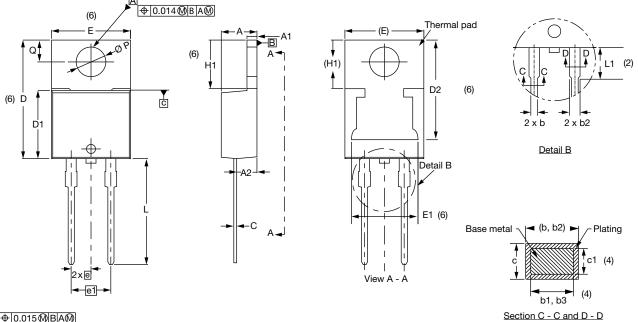
LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?96156			
Part marking information	www.vishay.com/doc?95391			



Vishay Semiconductors

TO-220AC 2L

DIMENSIONS in millimeters and inches



⊕0.015@BA@



SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
A	4.25	4.65	0.167	0.183	
A1	1.14	1.40	0.045	0.055	
A2	2.50	2.92	0.098	0.115	
b	0.69	1.01	0.027	0.040	
b1	0.38	0.97	0.015	0.038	4
b2	1.20	1.73	0.047	0.068	
b3	1.14	1.73	0.045	0.068	4
С	0.36	0.61	0.014	0.024	
c1	0.36	0.56	0.014	0.022	4
D	14.85	15.35	0.585	0.604	3
D1	8.38	9.02	0.330	0.355	

Conforms to JEDEC	® outline TO-220AC

SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
D2	11.68	13.30	0.460	0.524	6, 7
E	10.11	10.51	0.398	0.414	3, 6
E1	6.86	8.89	0.270	0.350	6
е	2.41	2.67	0.095	0.105	
e1	4.88	5.28	0.192	0.208	
H1	6.09	6.48	0.240	0.255	6
L	13.52	14.02	0.532	0.552	
L1	3.32	3.82	0.131	0.150	2
ØР	3.54	3.91	0.139	0.154	
Q	2.60	3.00	0.102	0.118	

Notes

 $^{(1)}\,$ Dimensioning and tolerancing as per ASME Y14.5M-1994

⁽²⁾ Lead dimension and finish uncontrolled in L1

⁽⁴⁾ Dimension b1, b3, and c1 apply to base metal only

(5) Controlling dimensions: inches

- ⁽⁶⁾ Thermal pad contour optional within dimensions E, H1, D2, and E1
- ⁽⁷⁾ Outline conforms to JEDEC[®] TO-220, except D2

Revision: 22-Feb-2024

1

⁽³⁾ Dimension D, D1, and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body



Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Hyperlinks included in this datasheet may direct users to third-party websites. These links are provided as a convenience and for informational purposes only. Inclusion of these hyperlinks does not constitute an endorsement or an approval by Vishay of any of the products, services or opinions of the corporation, organization or individual associated with the third-party website. Vishay disclaims any and all liability and bears no responsibility for the accuracy, legality or content of the third-party website or for that of subsequent links.

Vishay products are not designed for use in life-saving or life-sustaining applications or any application in which the failure of the Vishay product could result in personal injury or death unless specifically qualified in writing by Vishay. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

© 2025 VISHAY INTERTECHNOLOGY, INC. ALL RIGHTS RESERVED

Revision: 01-Jan-2025

1